

Rev.E May.-2016

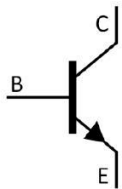
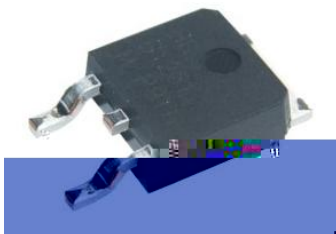
WR0585 1M E QSQ 1E M 4 s 11 1 Silicon NPN transistor in a TO-252 Plastic Package.

$H_f V_{CE0} I_{\alpha} \approx 10^4$

Low Collector–Emitter Saturation Voltage, High Current–Gain.

$f_{\alpha} \approx 100 \text{ kHz}$

Low power audio amplifier, Low current, high speed switching applications.



PIN1 1 Base

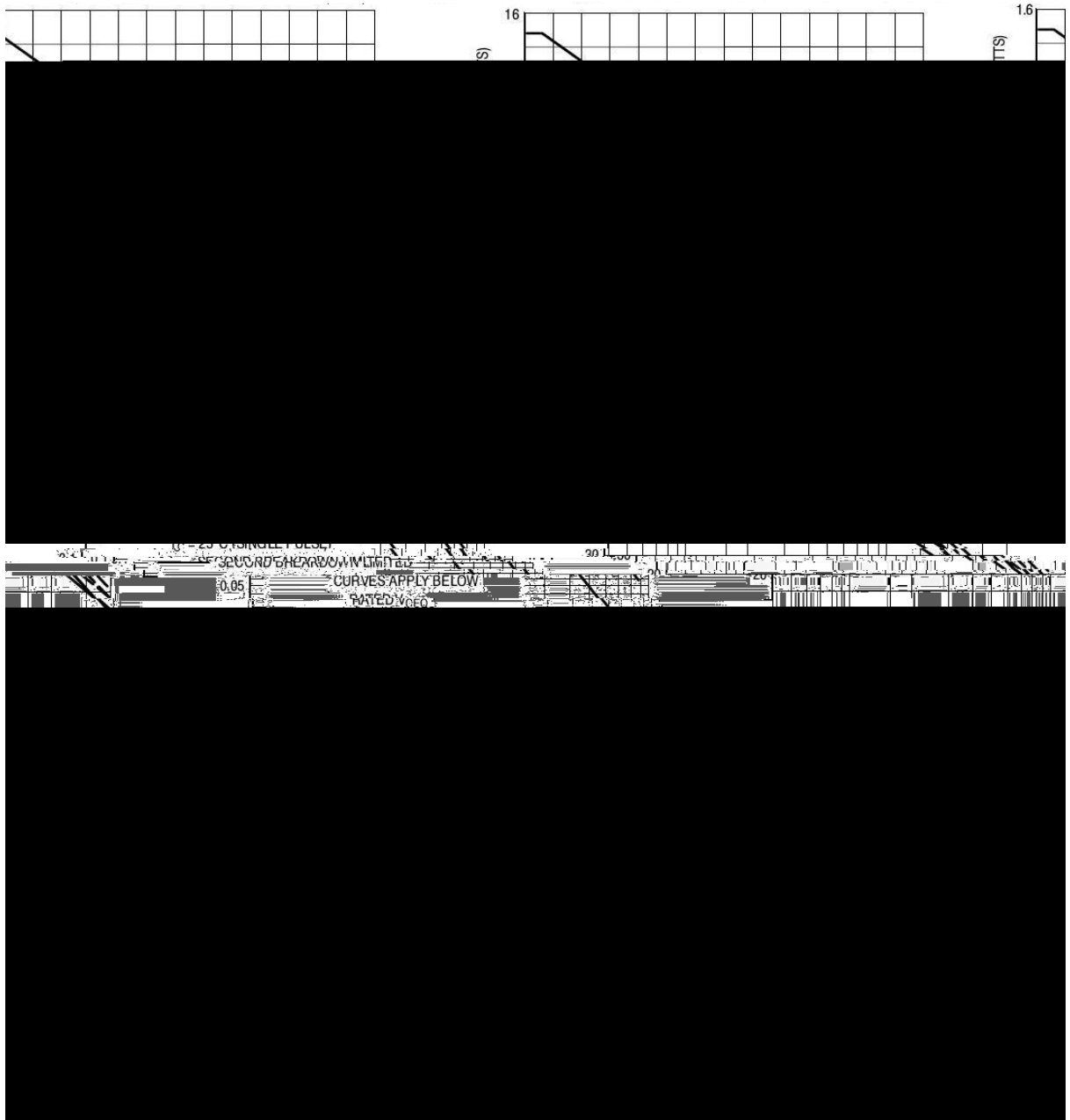
PIN 2,4 1 Collector

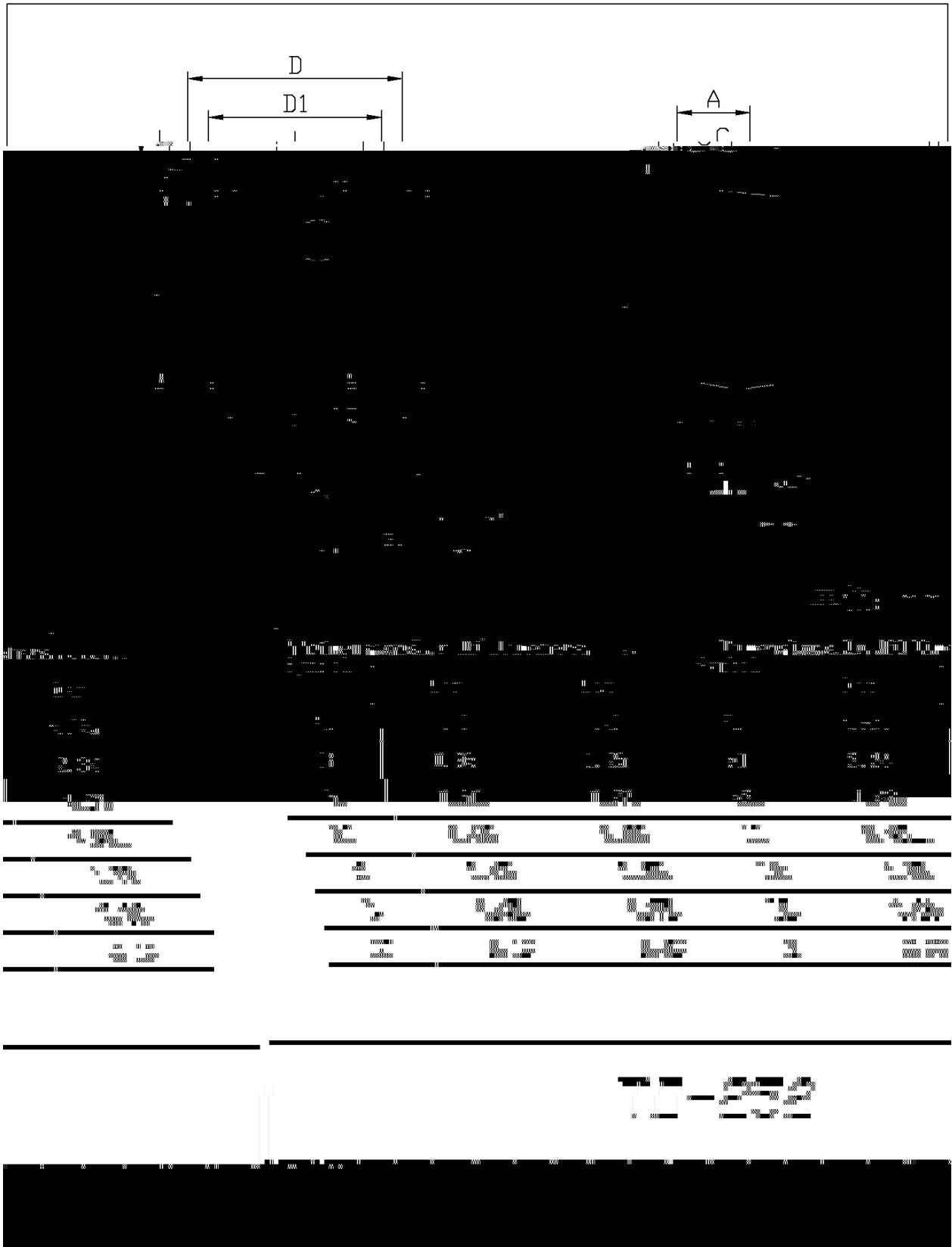
PIN 3 1 Emitter

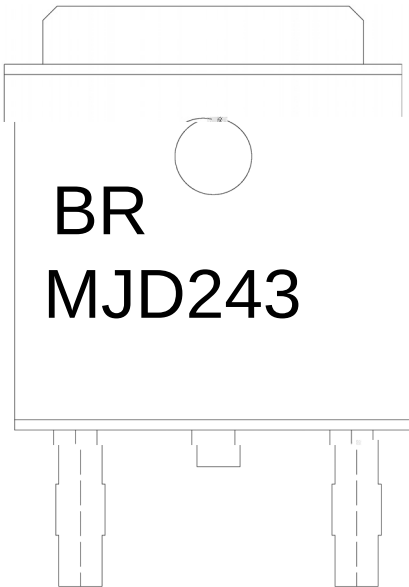
1 M 1 1 " See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	100	V
Collector to Emitter Voltage	V_{CEO}	100	V
Emitter to Base Voltage	V_{EBO}	7.0	V
Collector Current - Continuous	$I_{C(1)}$	4.0	A
Peak Collector Current - Continuous	$I_{C(2)}$	8.0	A
Base Current - Continuous	I_B	10	A
Collector Power Dissipation	P_D	1.4	W
Collector Power Dissipation	$P_D(T_c=25^\circ C)$	12.5	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 ~ 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=10mA$ $I_B=0$	100			V
Collector Cut-Off Current	$I_{CBO(1)}$	$V_{CB}=100V$ $I_E=0$			0.1	μA
	$I_{CBO(2)}$	$V_{CE}=100V$ $T_c=125$			0.1	mA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=-7.0V$ $I_C=0$			0.1	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=1.0V$ $I_C=200mA$	40		180	
	$h_{FE(2)}$	$V_{CE}=1.0V$ $I_C=1.0A$	15			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$ (1)	$I_C=500mA$ $I_B=50mA$			0.3	V

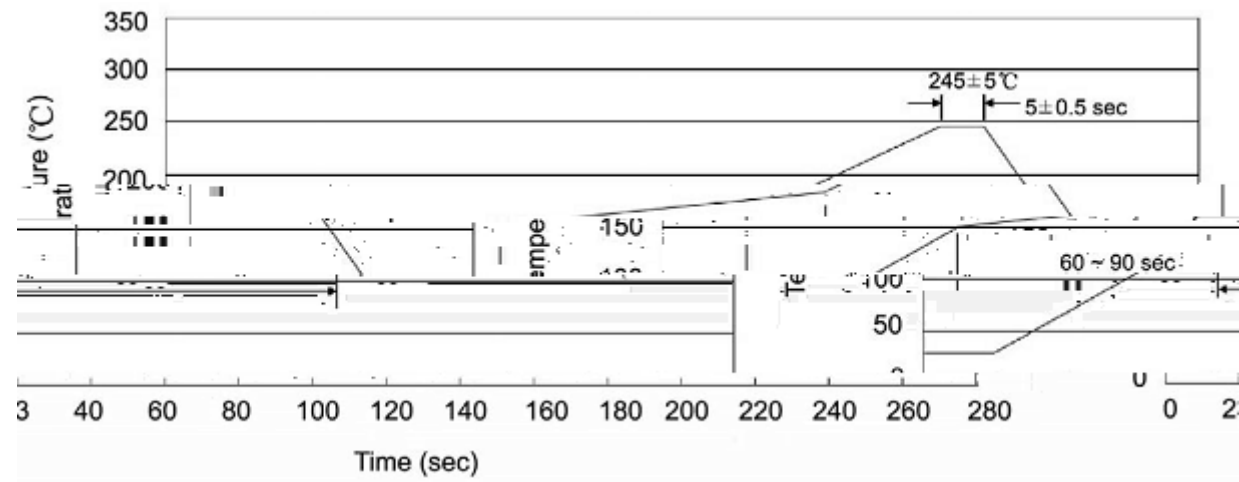






公司代码	公司代码
BR	公司代码
PMG576	公司代码
----	公司代码
Note:	
BR:	Company Code
MJD243:	Product Type.
****:	Lot No. Code, code change with Lot No.

Temperature Profile for IR Reflow Soldering(Pb-Free)



注意

1. 升温：25~150℃，时间：60~90sec；
2. 峰值温度：245±5℃，时间：5±0.5sec；
3. 冷却速度：2~10℃/sec。

Note:

- 1.Preheating:25~150℃，Time:60~90sec.
- 2.Peak Temp.:245±5℃，Duration:5±0.5sec.
3. Cooling Speed: 2~10℃/sec.

峰值温度：260±5℃ 时间：10±1 sec. Temp.:260±5 Time:10±1 sec

尺寸 / REEL

Package Type	Units					Dimension (unit mm ³)		